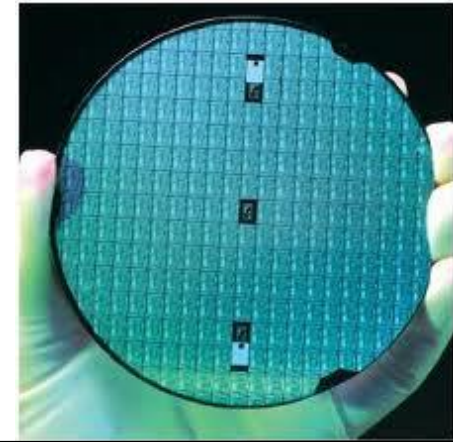
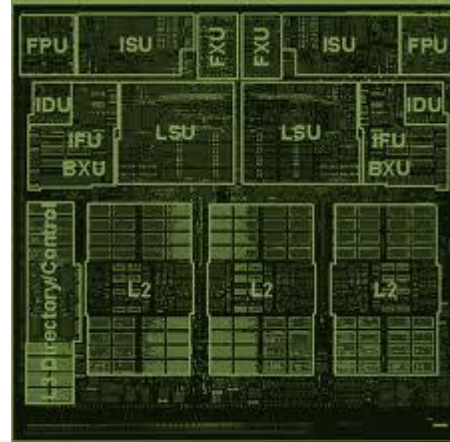
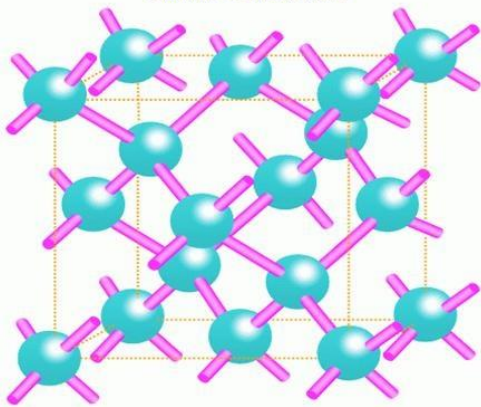


Structure of silicon crystal



ECE 122A

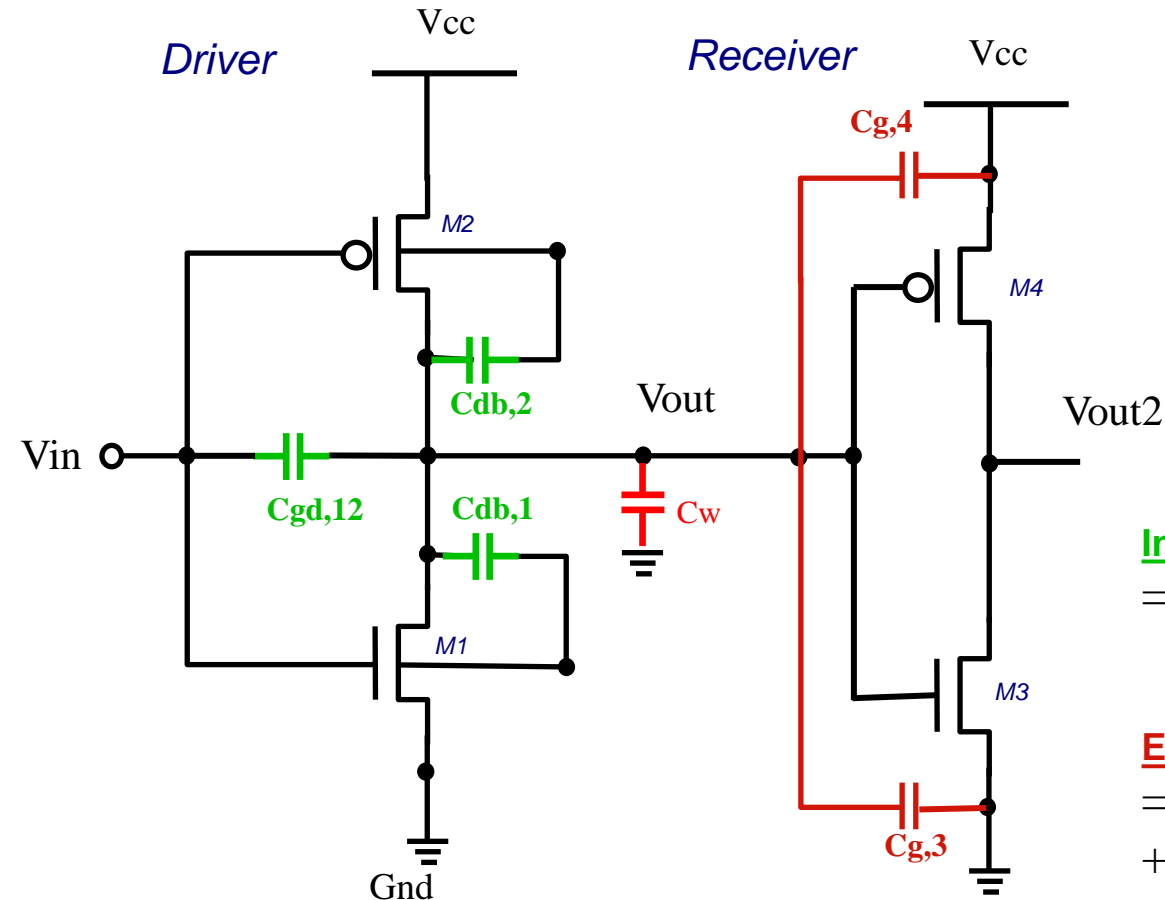
VLSI Principles

Lecture 10

Prof. Kaustav Banerjee
Electrical and Computer Engineering
University of California, Santa Barbara
E-mail: kaustav@ece.ucsb.edu

Inverter Sizing

Load capacitances



$$C_L = C_{int} + C_{ext}$$

Internal Caps of Driver (C_{int}):

= Junction caps: $C_{db,12} +$

Gate caps: $C_{gd,12}$ (including Miller Caps.)

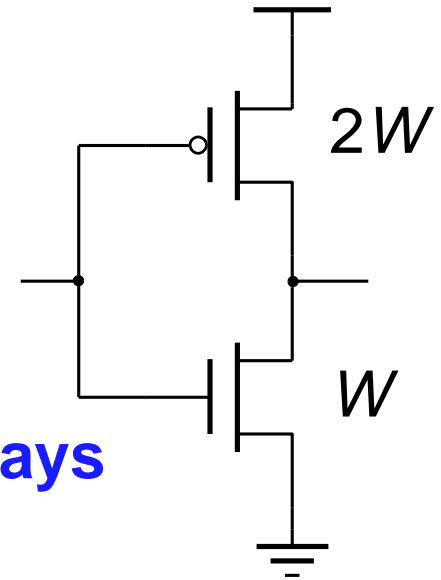
External Caps (C_{ext}):

= Interconnect cap: C_w

+ Receiver gate caps: $C_{g,43}$

Inverter Delay

- Minimum length devices, $L=0.25\mu\text{m}$
- Assume that for $W_P = 2W_N = 2W$
 - same pull-up and pull-down currents
 - approx. equal resistances $R_N = R_P$
 - approx. **equal rise t_{pLH} and fall t_{pHL} delays**
- Analyze as an RC network



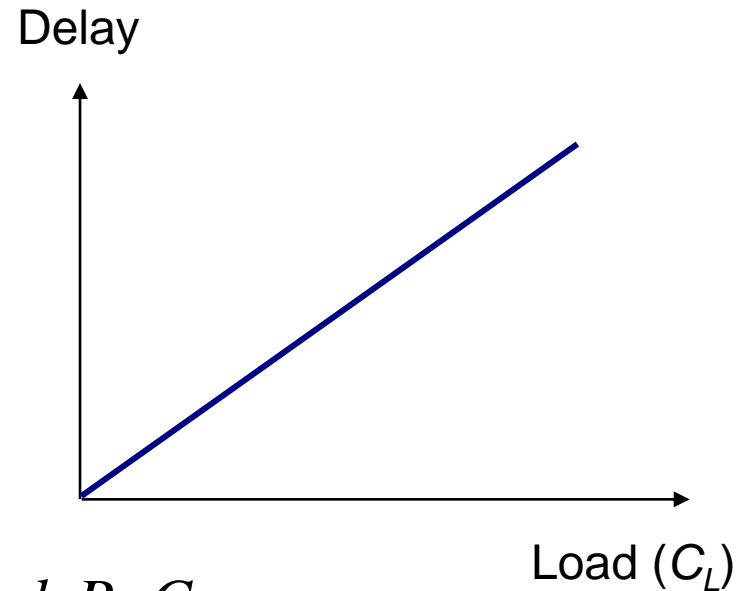
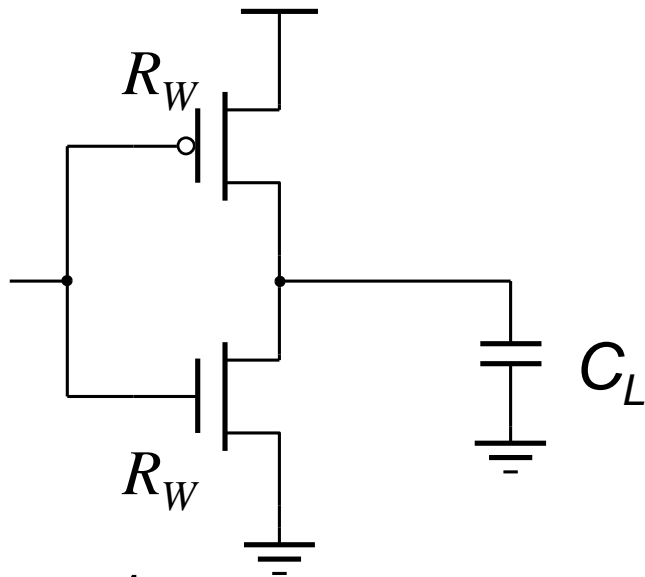
Delay (D): $t_{pHL} = (\ln 2) R_N C_L$

$t_{pLH} = (\ln 2) R_P C_L$

Load for previous stage: $C_{gin} = 3 \frac{W}{W_{unit}} C_{unit}$

W_{unit} and C_{unit} correspond to an unit size (minimum size) device...

Inverter with Load



$$W_{unit} = 1$$

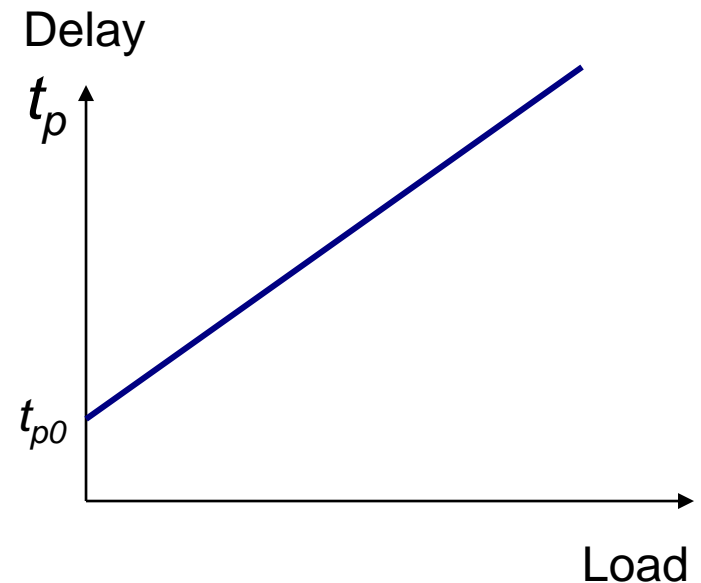
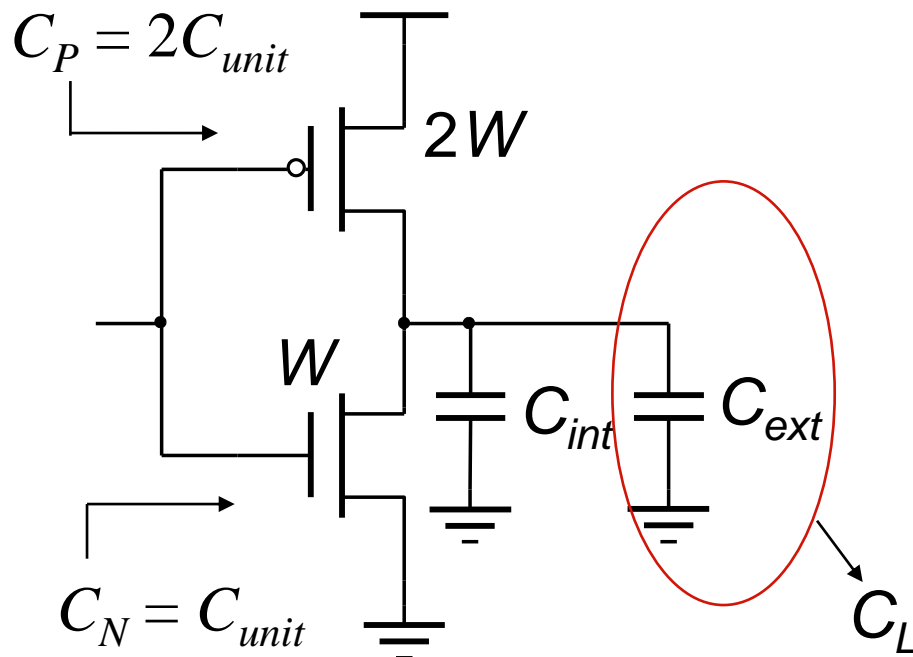
$$t_p = (t_{pHL} + t_{pLH})/2 = k R_W C_L$$

k is a constant, equal to 0.69

Note: $R_p = R_n = R_W$
Hence, $(R_p + R_n)/2 = R_W$

Assumptions: no load \longrightarrow zero delay?

Inverter with Load



$$\text{Delay } (t_p) = kR_W(C_{int} + C_{ext}) = kR_W C_{int} + kR_W C_{ext} = \underbrace{kR_W C_{int}}_{t_{p0} \text{ (intrinsic delay)}} (1 + C_{ext}/C_{int})$$

This is the net internal cap.

Intrinsic delay of CMOS inverter

Let R_{eq} be the equivalent resistance of the gate (inverter), then delay (t_p) is defined as:

$$\begin{aligned}t_p &= 0.69 R_{eq} (C_{int} + C_{ext}) \\&= 0.69 R_{eq} C_{int} \left(1 + \frac{C_{ext}}{C_{int}} \right) \\&= t_{p0} \left(1 + \frac{C_{ext}}{C_{int}} \right)\end{aligned}$$

t_{p0} is the **intrinsic** delay

Impact of sizing on gate delay

Let S be the sizing factor

R_{ref} be the resistance of a reference gate (usually a minimum size gate)

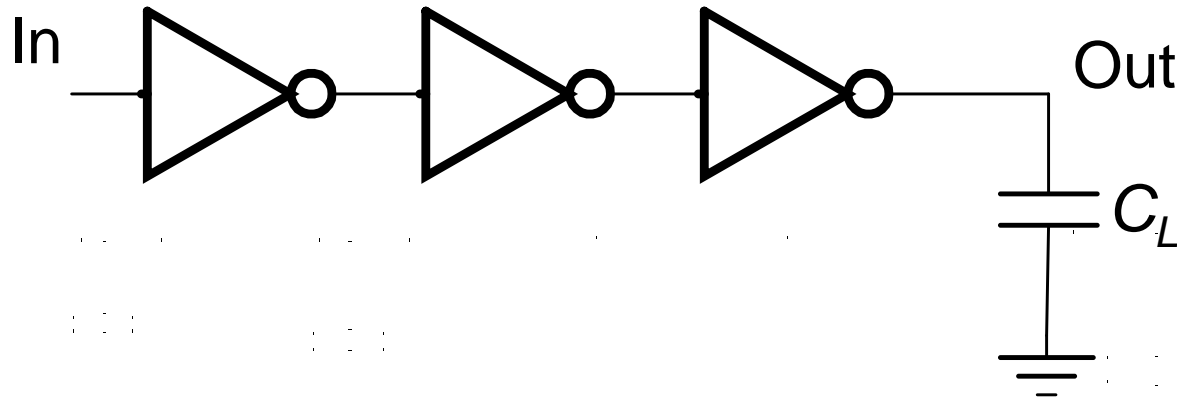
C_{iref} be the internal capacitance of the reference gate

$$\begin{aligned}C_{int} &= S C_{iref}, \quad R_{eq} = \frac{R_{ref}}{S} \\t_p &= 0.69 \left(\frac{R_{ref}}{S} \right) (S C_{iref}) \left(1 + \frac{C_{ext}}{S C_{iref}} \right) \\&= 0.69 R_{ref} C_{iref} \left(1 + \frac{C_{ext}}{S C_{iref}} \right) \\&= t_{p0} \left(1 + \frac{C_{ext}}{S C_{iref}} \right)\end{aligned}$$

Hence:

1. Intrinsic delay is independent of gate sizing, and is determined only by technology and inverter layout
2. If S is made very large, gate delay approaches the intrinsic value but increases the area significantly

Inverter Chain

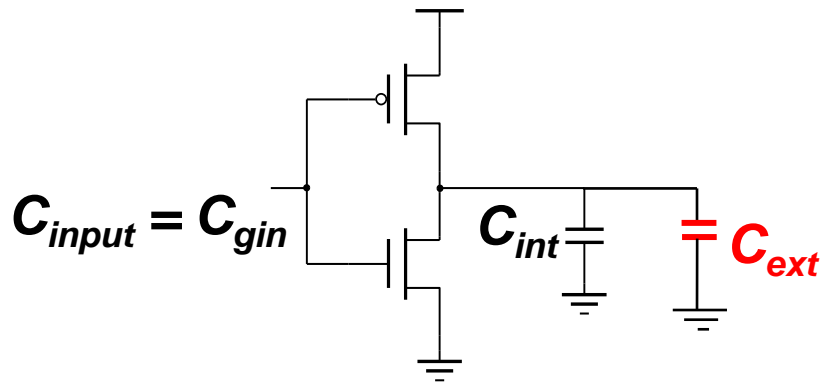


If C_L is given:

- How many stages are needed to minimize the delay?
- How to size the inverters?

May need some additional constraints....

Delay Formula: inverter chain



Let $C_{int} = \gamma C_{gin}$ with $\gamma \approx 1$

$f = C_{ext}/C_{gin}$ - effective fanout

$$\text{Delay} \sim R_{eq} (C_{int} + C_{ext})$$

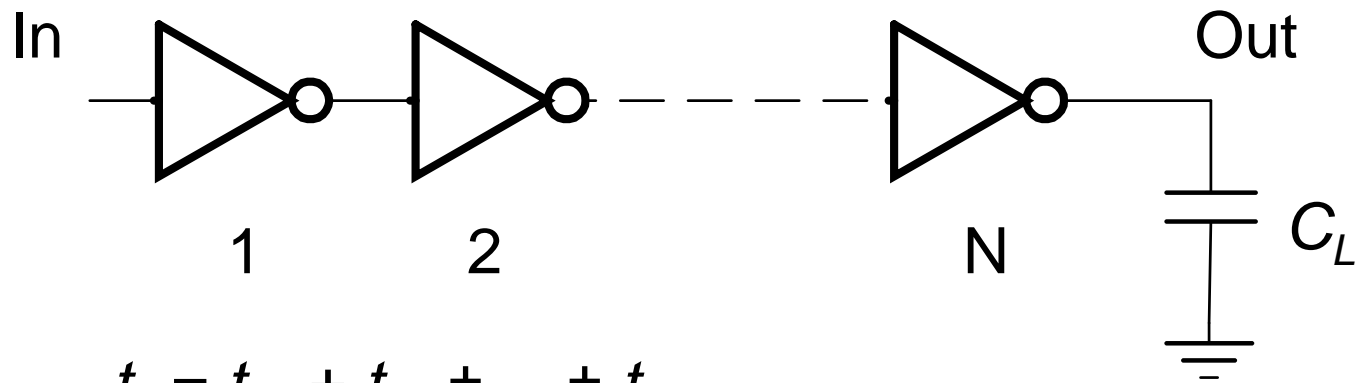
Inverter delay is only a function of the **RATIO** between C_{ext} and C_{input}

$$t_p = 0.69 R_{eq} C_{int} \left(1 + C_{ext} / \gamma C_{gin} \right) = t_{p0} (1 + f / \gamma)$$

t_{p0}

relates the input gate cap. (C_{gin}) and the intrinsic output cap. (C_{int}) of the inverter...

Apply to Inverter Chain



$$t_p = t_{p1} + t_{p2} + \dots + t_{pN}$$

$$t_{p,j} = t_{p0} \left(1 + \frac{C_{gin,j+1}}{\gamma C_{gin,j}} \right)$$

← This is C_{ext} for the j^{th} gate
← This is C_{int} for the j^{th} gate

$$t_p = \sum_{j=1}^N t_{p,j} = t_{p0} \sum_{j=1}^N \left(1 + \frac{C_{gin,j+1}}{\gamma C_{gin,j}} \right), \quad C_{gin,N+1} = C_L$$

Optimal Tapering for Given N

Delay equation has $N - 1$ unknowns, $C_{g,2} \dots C_{g,N}$

Minimize the delay, find $N - 1$ partial derivatives and equate them to zero, or $\left(\frac{\partial t_p}{\partial C_{g,j}} \right) = 0$

Result: $C_{g,j+1}/C_{g,j} = C_{g,j}/C_{g,j-1}$ With $j = 2, \dots, N$

Size of each stage is the geometric mean of two neighbors

$$C_{g,j} = \sqrt{C_{g,j-1}C_{g,j+1}}$$

- each stage has the same effective fanout ($f_j = f = C_{ext}/C_{g,j}$)
- hence, each stage has the same delay: $t_p = t_{p0} (1 + f/\gamma)$

Optimum Delay and Number of Stages

When each stage is sized by f and has same eff. fanout f :

$$\frac{C_L}{C_{g,N}} = \frac{C_{g,N}}{C_{g,N-1}} = \dots = \frac{C_{g,2}}{C_{g,1}} = f$$

(multiplying all the terms) Hence, $f^N = C_L / C_{g,1} = F$

F is the overall effective fanout of the circuit

Effective fanout of each stage: $f = \sqrt[N]{F}$ **If C_L and $C_{g,1}$ are known....**

Minimum path delay:

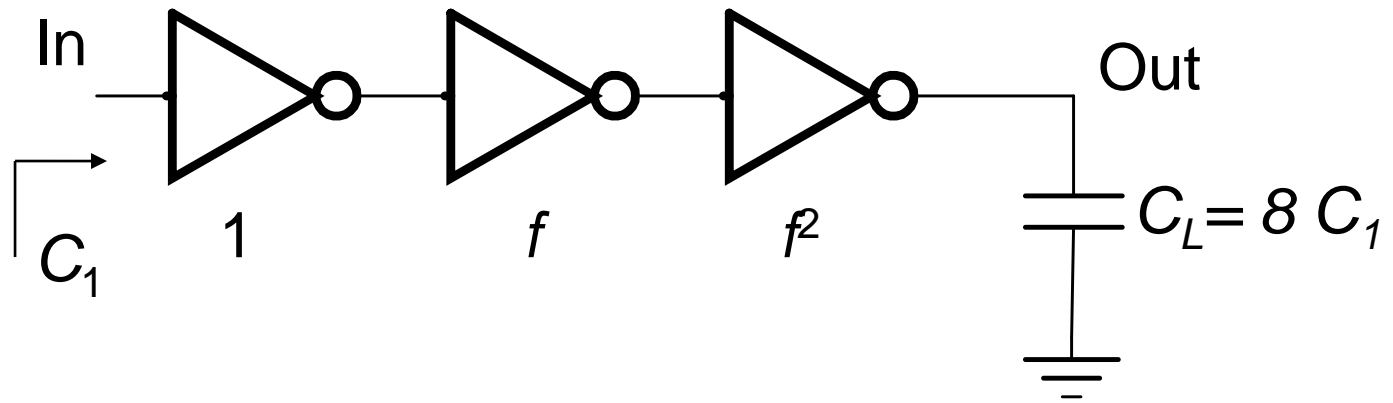
$$t_p = Nt_{p0} \left(1 + \sqrt[N]{F} / \gamma \right)$$

If N is too large, intrinsic delay of stages dominate, while if N is small, effective fanout of each stage (f) is large and the second term dominates

How to choose N ?

Example

If N is given....



C_L/C_1 has to be evenly distributed across $N = 3$ stages:

$$F = (8C_1)/C_1 = 8 \qquad f = \sqrt[3]{8} = 2$$

Optimum Number of Stages

For a given load, C_L and given input capacitance C_{in}
Find optimal sizing f

$$C_L = F \cdot C_{in} = f^N C_{in} \text{ with } N = \frac{\ln F}{\ln f}$$

$$t_p = N t_{p0} \left(F^{1/N} / \gamma + 1 \right) = \frac{t_{p0} \ln F}{\gamma} \left(\frac{f}{\ln f} + \frac{\gamma}{\ln f} \right)$$

$$\frac{\partial t_p}{\partial f} = \frac{t_{p0} \ln F}{\gamma} \cdot \frac{\ln f - 1 - \gamma / f}{\ln^2 f} = 0$$

If self-loading is ignored....

For $\gamma = 0$, $f = e = 2.718$, $N = \ln F$

Otherwise....

$$f = \exp(1 + \gamma / f)$$

Optimum Effective Fanout f

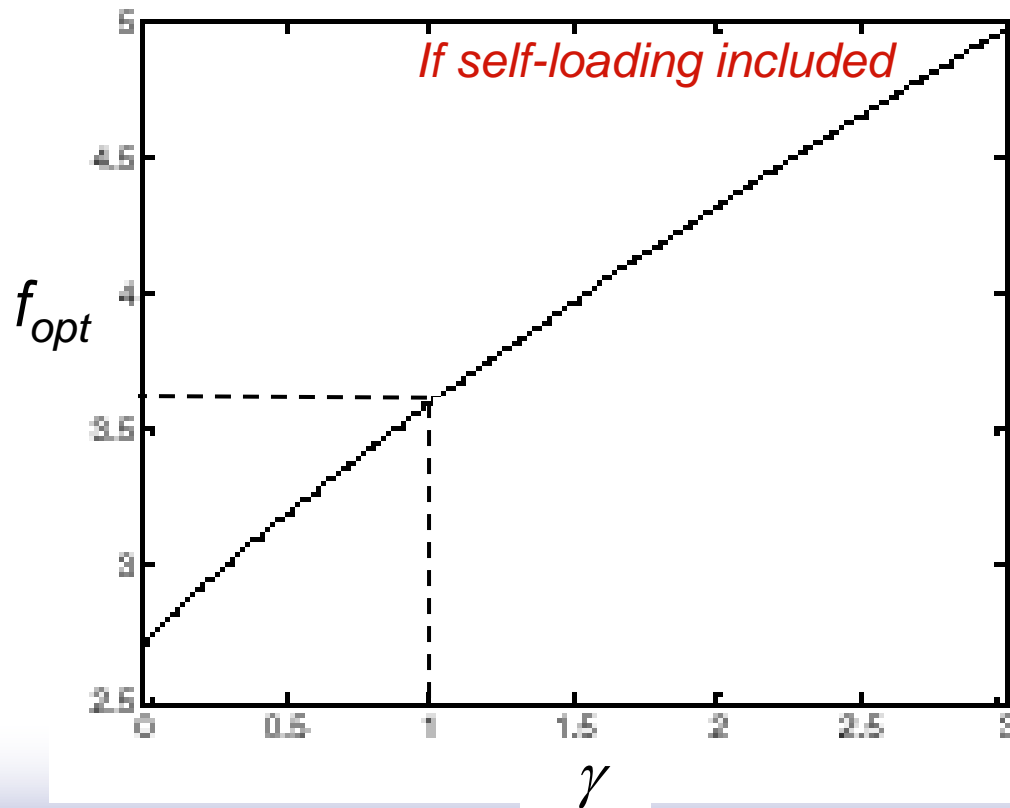
Optimum f for given process defined by γ

$$f = \exp(1 + \gamma/f)$$

Optimum
tapering factor:

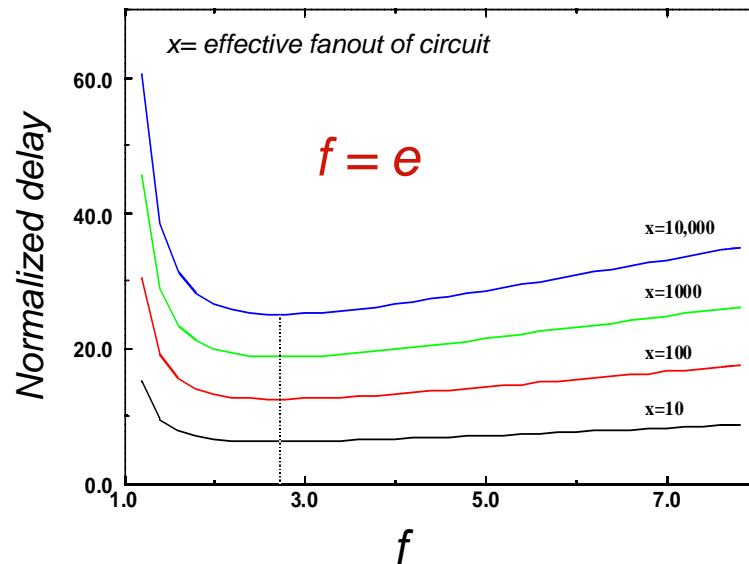
$$f_{opt} = 3.6$$

for $\gamma=1$ (typical case)



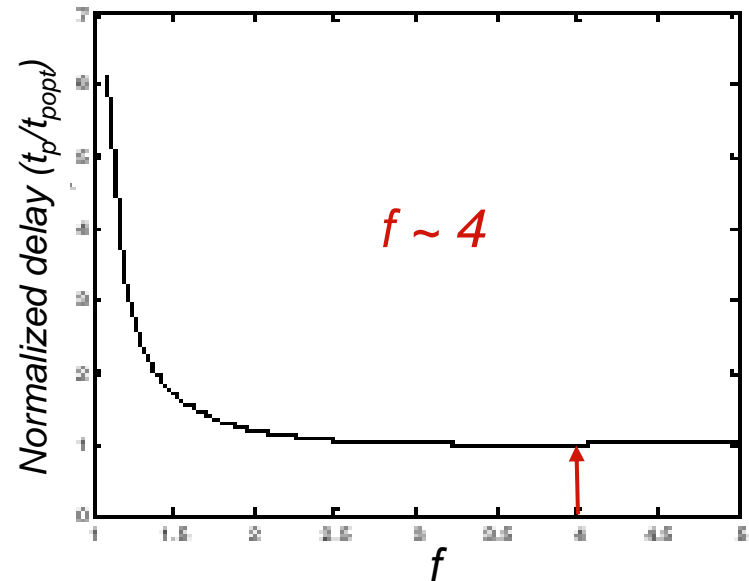
Impact of Self-Loading on t_p

No Self-Loading, $\gamma=0$



Optimal number of stages, $N = \ln(F)$

With Self-Loading $\gamma=1$



If $f < f_{opt}$ (too many stages) will result in delay to increase

Normalized delay function of F

$$t_p = Nt_{p0} \left(1 + \sqrt[N]{F} / \gamma \right)$$

$$t_{popt}/t_{p0} \text{ for } \gamma=1$$

F	Unbuffered	Two Stage	Inverter Chain
10	11	8.3	8.3
100	101	22	16.5
1000	1001	65	24.8
10,000	10,001	202	33.1

As F increases, the differences between the unbuffered case (or two-stage buffer case) and the case of inverter chain increases.....

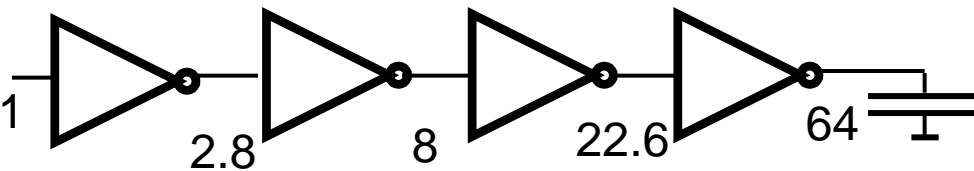
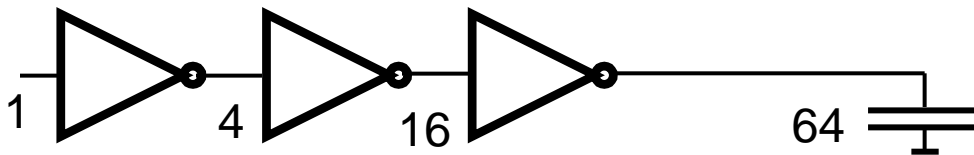
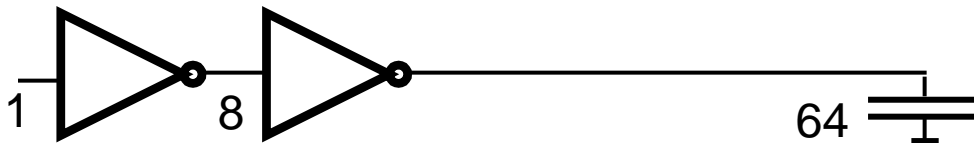
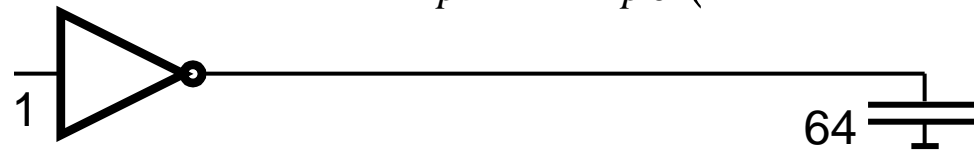
Buffer Design

$$t_p = N t_{p0} \left(1 + \sqrt[N]{F} / \gamma \right)$$

$$f = F^{1/N}$$

t_{popt}/t_{p0} for $\gamma=1$

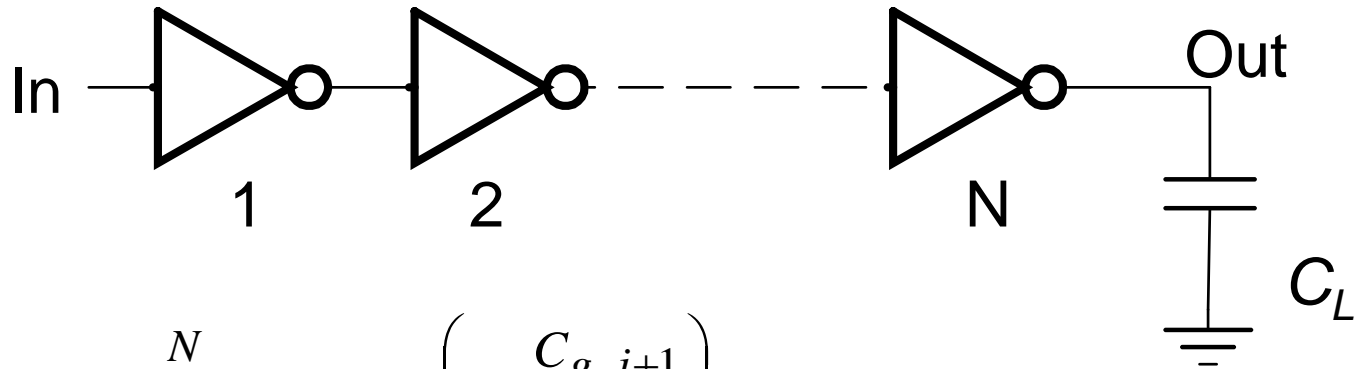
N	f	t _p
1	64	65
2	8	18
3	4	15
4	2.8	15.3



Sizing Logic Paths for Speed

- ❑ Frequently, input capacitance of a logic path is constrained
- ❑ Logic also has to drive some capacitance
- ❑ Example: ALU load in an Intel's microprocessor is 0.5pF
- ❑ How do we size the ALU datapath to achieve maximum speed?
- ❑ We have already solved this for the inverter chain – can we generalize it for any type of logic?

Buffer Example



$$\text{Chain Delay} = \sum_{j=1}^N t_{p,j} = t_{p0} \left(1 + \frac{C_{g,j+1}}{\gamma C_{g,j}} \right), \text{ with } C_{g,N+1} = C_L$$

(in units of τ_{inv})

For given N : $C_{g,j+1}/C_{g,j} = C_{g,j}/C_{g,j-1}$

Optimal fanout (f): $C_{g,j+1}/C_{g,j} \sim 4$

How to generalize this to any logic path?

Minimizing Delay in Complex Logic Networks

$$\begin{aligned} \text{Delay} &= t_{p0} \left(1 + \frac{f}{\gamma} \right) \text{ (inverter)} \\ &= t_{p0} \left(p + \frac{g \cdot f}{\gamma} \right) \text{ (Complex gate)} \end{aligned}$$

Everything Normalized w.r.t an inverter:

$$g_{inv} = 1, p_{inv} = 1$$

f – effective fanout (*ratio of external load and input cap. of gate*)

p – ratio of intrinsic delays of complex gate and inverter
(value increases with complexity of gate)

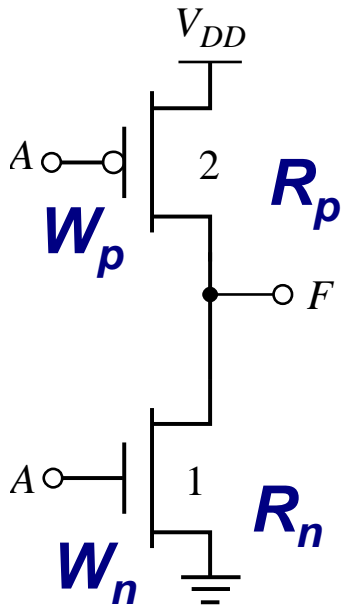
g – logical effort: how much more input capacitance is presented by the complex gate to deliver the same output current as an inverter (depends only on circuit topology)

Logical Effort

- ❑ Inverter has the smallest logical effort and intrinsic delay of all static CMOS gates
- ❑ Logical effort of a gate is the ratio of its input capacitance to the inverter capacitance when sized to deliver the same current
- ❑ Logical effort increases with gate complexity

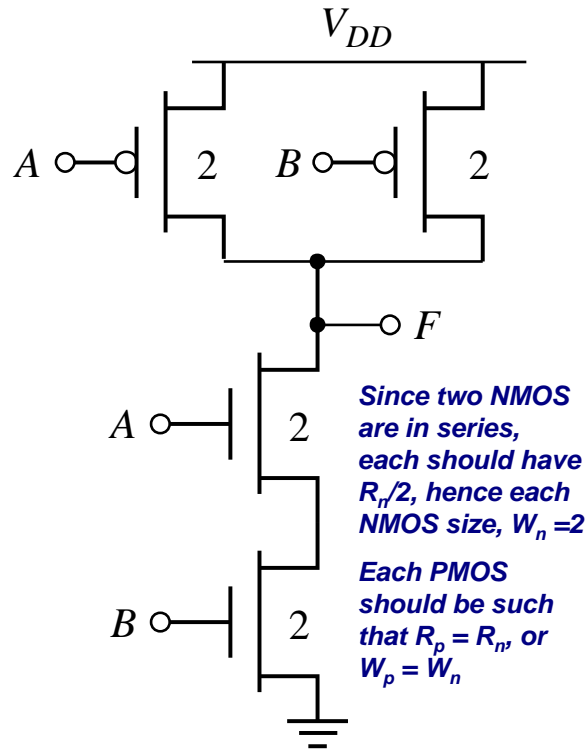
Logical Effort

Logical effort is the ratio of input capacitance of a gate to the input capacitance of an inverter with the **same output current**



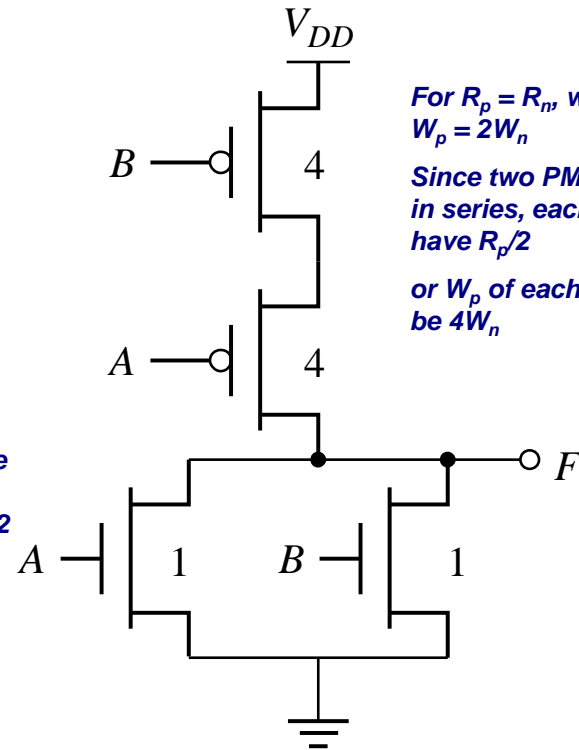
Inverter

$$g = 1$$



2-input NAND

$$g = 4/3$$



2-input NOR

$$g = 5/3$$

For $R_p = R_n$, we need $W_p = 2W_n$

Since two PMOS are in series, each should have $R_p/2$

or W_p of each should be $4W_n$

Delay in a Logic Gate

Gate delay:

$$d = h + p$$

effort delay intrinsic delay

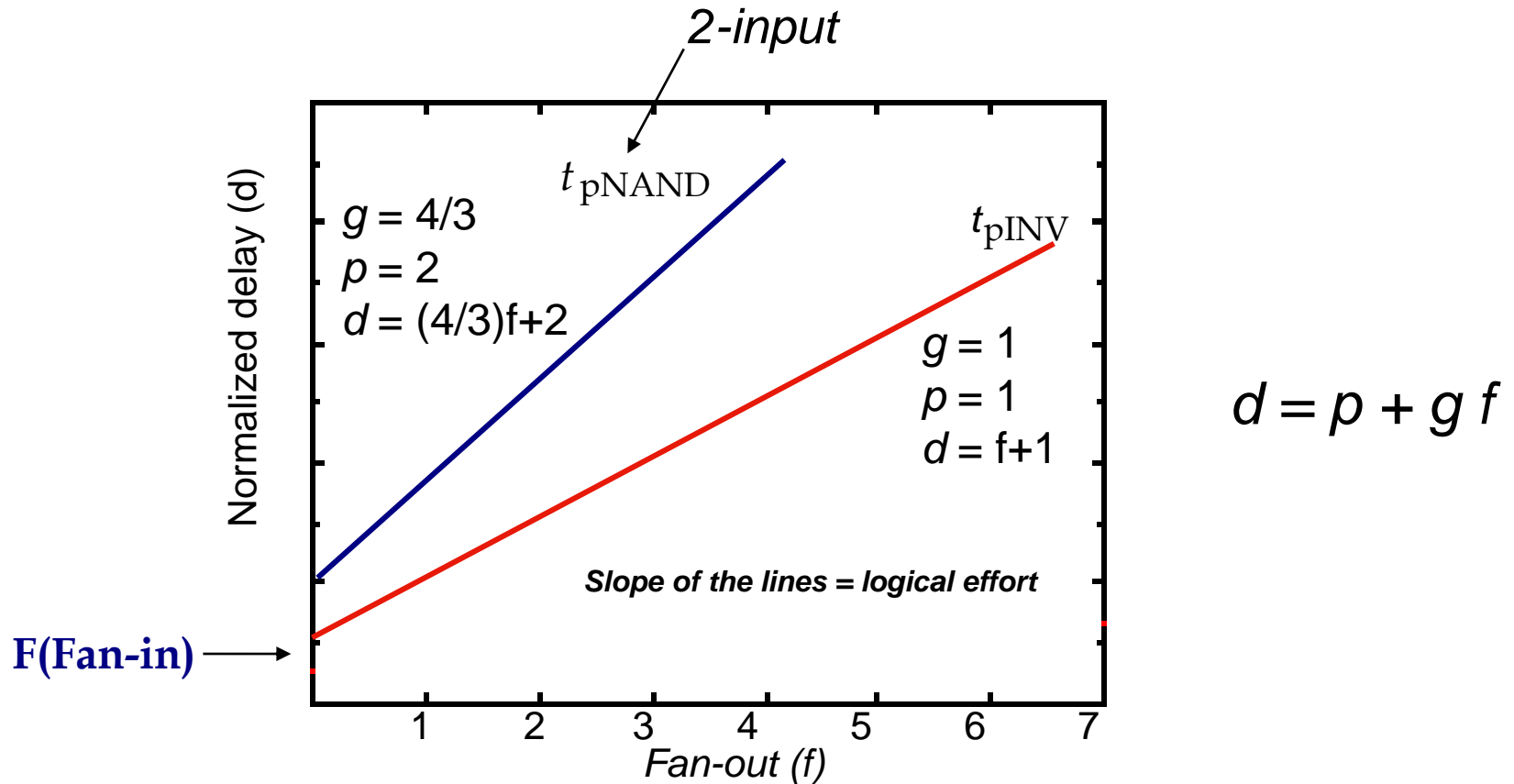
Effort delay (or gate effort):

$$h = g f$$

logical effort effective fanout = C_{ext}/C_{in}

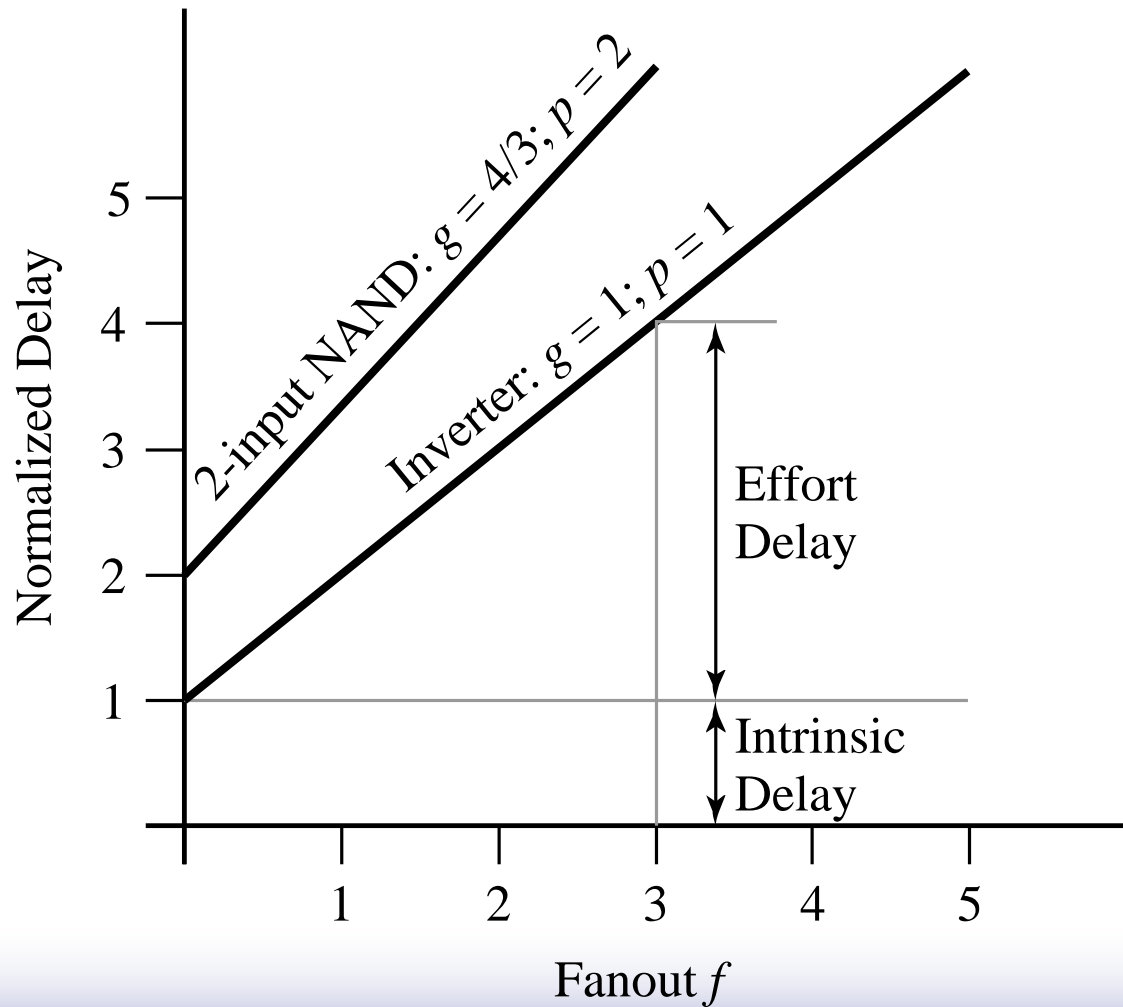
- **Logical effort** is a function of topology, independent of sizing
- Effective fanout (**electrical effort**) is a function of load/gate size

Logical Effort of Gates



- **Delay can be adjusted by:**
 - *transistor sizing that changes the effective fanout*
 - *Choosing a gate with different g*

Logical Effort of Gates



Logical Effort

Gate Type	Number of Inputs			
	1	2	3	n
Inverter	1			
NAND		$4/3$	$5/3$	$(n + 2)/3$
NOR		$5/3$	$7/3$	$(2n + 1)/3$
Multiplexer		2	2	2
XOR		4	12	

From Sutherland, Sproull

Total delay through a combinational logic block

$$t_p = \sum_{j=1}^N t_{p,j} = t_{p0} \sum_{j=1}^N \left(p_j + \frac{f_j g_j}{\gamma} \right)$$

Similar to inverter chain delay....find N-1 partial derivatives and equate them to zero....

For minimal delay : $g_1 f_1 = g_2 f_2 = \dots = g_N f_N$ (each stage should have the same gate effort, h)

$$\text{Path Logic Effort} = G = \prod_1^N g_i$$

$$\text{Path Effective Fanout} = F = \frac{C_L}{C_{g1}}$$

(or Path Electrical Effort)

Note: In the text book, this is defined as H

Branching Effort

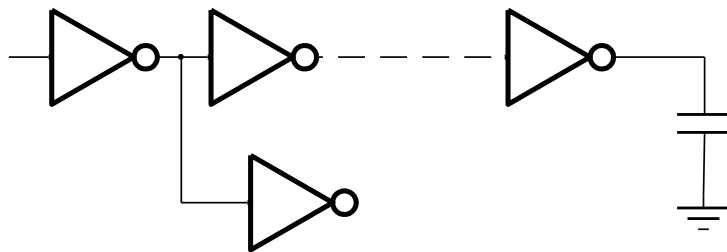
To relate F to the effective fanouts of the individual gates, one must account for the logical fanout within the network

When fanout occurs at the output of a node, some of the available drive current is directed along the path being analyzed

Branching effort of a logic gate:

$$b = \frac{C_{on-path} + C_{off-path}}{C_{on-path}}$$

Load capacitance of the gate along the path under study



$$\text{Path Branching Effort} = B = \prod_{1}^N b_i$$

Total Path Effort

- Path electrical effort can be related to the electrical and branching efforts of the individual gates:

$$F = \prod_1^N \frac{f_i}{b_i} = \frac{\prod f_i}{B}$$

- Total path effort can be defined as:

$$H = \prod_1^N h_i = \prod_1^N g_i f_i = GFB$$

Note: In the text book, H and F have been swapped...

- Gate effort that minimizes the path delay = ?
- Minimum delay through path = ?

Multistage Networks

$$Delay = \sum_{i=1}^N (p_i + g_i \cdot f_i)$$

Gate effort: $h_i = g_i f_i$

Path electrical effort: $F = C_L / C_{gin}$

Path logical effort: $G = g_1 g_2 \dots g_N$

Path branching effort: $B = b_1 b_2 \dots b_N$

*Path effort: $H = GFB$

Path delay $D = \sum d_i = \sum p_i + \sum h_i$

*** Note: In the text book, this is defined as: $F = GHB$**

Optimal Number of Stages

For a given load,
and given input capacitance of the first gate
Find optimal number of gates and optimal sizing

$$D = NH^{1/N} + Np_{inv}$$

$$\frac{\partial D}{\partial N} = -H^{1/N} \ln(H^{1/N}) + H^{1/N} + p_{inv} = 0$$

Substitute 'best gate effort': $h = H^{1/N}$  Gate effort that minimizes path delay

A path achieves least delay by using $N = \log_4 H$ stages

Optimum Effort per Stage

When each stage bears the same effort:

$$h^N = H$$

$$h = \sqrt[N]{H}$$

gate efforts: $g_1 f_1 = g_2 f_2 = \dots = g_N f_N$

Effective fanout of each gate: $f_i = h / g_i$

Minimum path delay:

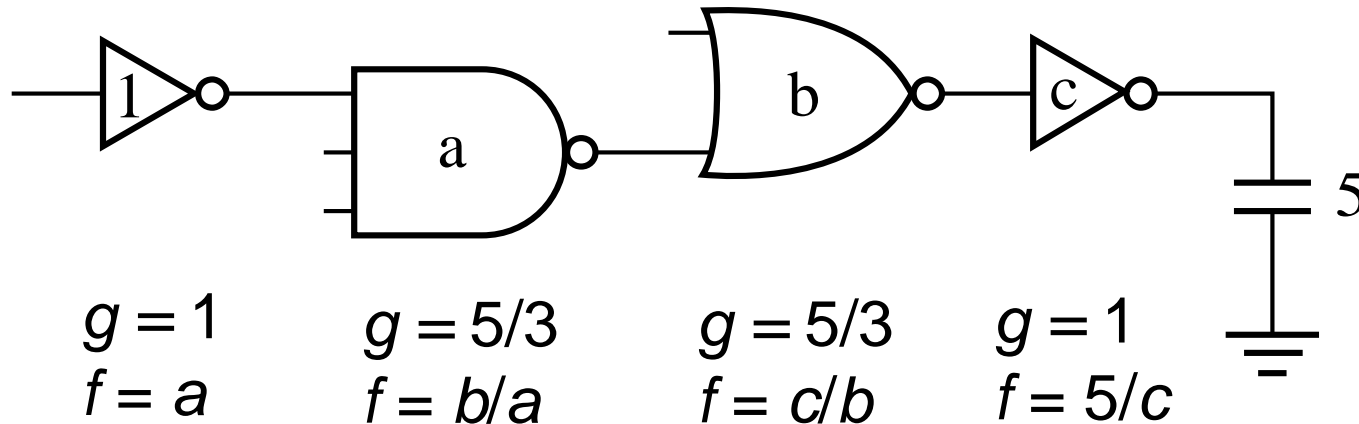
$$D = t_{p0} \left(\sum_{j=1}^N p_j + \frac{N \left(\sqrt[N]{H} \right)}{\gamma} \right)$$

Sizing of Chain of Gates

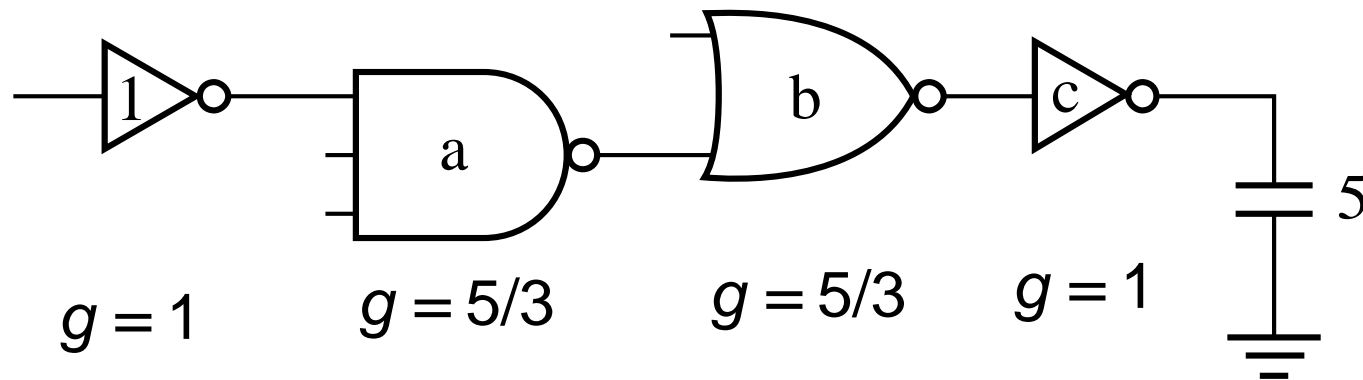
- Consider chain s_i
- Sizing factors for each gate in the chain can be derived by working out from front to end (or vice versa).
- Assume that a unit-size gate has a driving capability equal to a minimum-size inverter
- Hence, $C_{gin} = g C_{in_ref}$
- If s_1 is the sizing factor for gate 1:
 - $C_{g1} = s_1 g_1 C_{in_ref}$
 - Input capacitance of gate 2 is larger by f_1/b_1 :
That is, $C_{g2} = f_1/b_1 C_{g1} = s_2 g_2 C_{in_ref}$
 - For gate i in the chain:

$$s_i = \left(\frac{g_1 s_1}{g_i} \right) \prod_{j=1}^{i-1} \left(\frac{f_j}{b_j} \right)$$

Example: Optimize Path



Example: Optimize Path



Effective fanout, $F = 5/1 = 5$
 $G = 1 \times 5/3 \times 5/3 \times 1 = 25/9$
 $B=1$ (no branching)
 $H = GFB = 125/9 = 13.9$
 $h = H^{1/4} = 1.93$ (optimal gate effort)

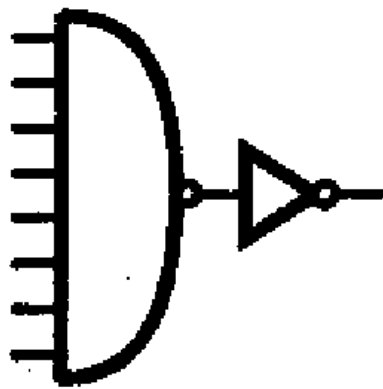
Derive Fanout Factors (taking gate types into account):

$f_1 = 1.93$ (since $h=gf$)
 $f_2 = 1.93 (3/5) = 1.16$
 $f_3 = 1.16$
 $f_4 = 1.93$

Derive Gate Sizes:

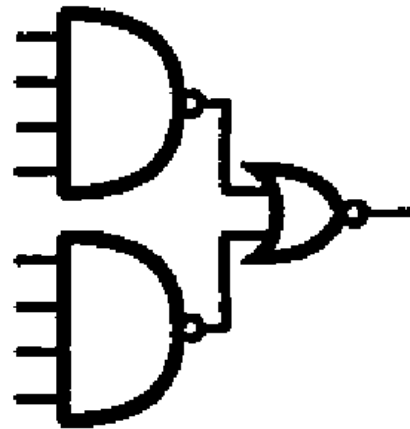
$a = f_1 g_1 / g_2 = 1.16$
 $b = f_1 f_2 g_1 / g_3 = 1.34$
 $c = f_1 f_2 f_3 g_1 / g_4 = 2.6$

Example – 8-input AND



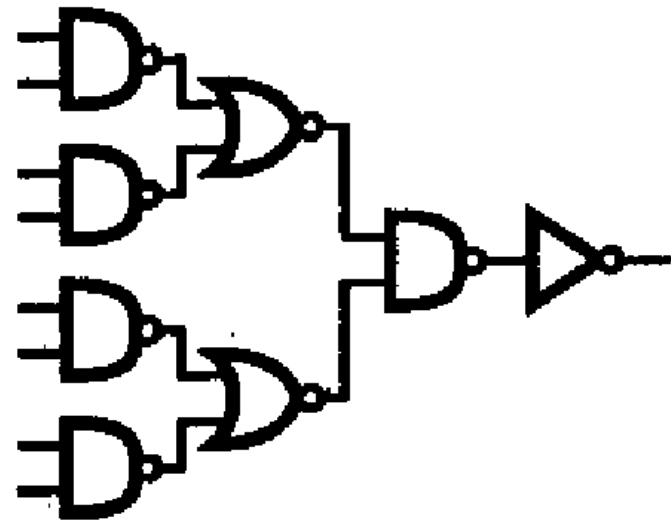
$$g=10/3 \quad g=1$$

(a)



$$g=2 \quad g=5/3$$

(b)



$$g=4/3 \quad g=5/3 \quad g=4/3 \quad g=1$$

(c)

Method of Logical Effort

- Compute the path effort: $H = GFB$
- Find the best number of stages $N \sim \log_4 H$
- Compute the stage effort $h = H^{1/N}$
- Sketch the path with this number of stages
- Work from either end, find sizes:

$$C_{in} = C_{out} * g/h$$

Reference: Sutherland, Sproull, Harris, "Logical Effort, Morgan-Kaufmann 1999.

Summary

Table 4: Key Definitions of Logical Effort

Term	Stage expression	Path expression
Logical effort	g	$G = \prod g_i$
Electrical effort	$f = \frac{C_{out}}{C_{in}}$	$F = \frac{C_{out (path)}}{C_{in (path)}}$
Branching effort	n/a	$B = \prod b_i$
Effort	$h = gf$	$H = GFB$
Effort delay	h	$D_H = \sum h_i$
Number of stages	1	N
Parasitic delay	p	$P = \sum p_i$
Delay	$d = h + p$	$D = D_H + P$

Sutherland,
Sproull and
Harris